

No.2970

2 S C 4 2 7 2

NPN Epitaxial Planar Silicon Transistor

27MHz CB Transceiver Driver Applications

Features

· Small size making it easy to provide high-density, small-sized hybrid ICs.

| Absolute Maximum Ratings | at $Ta = 2$ | 25°C | | unit |
|------------------------------|------------------|---|-----|----------------------|
| Collector to Base Voltage | V_{CBO} | | 75 | V |
| Collector to Emitter Voltage | VCER | $R_{BE} = 150\Omega$ | 75 | V |
| Collector to Emitter Voltage | | | 45 | V |
| Emitter to Base Voltage | VEBO | | 5 | V |
| Collector Current | $I_{\mathbf{C}}$ | | 1.0 | Α |
| Collector Current(Pulse) | I _{CP} | | 1.5 | Α |
| Collector Dissipation | P_{C} | Mounted on ceramic board $(250 \text{mm}^2 \times 0.8 \text{mm})$ | 1.3 | W |
| Junction Temperature | Tj | | 150 | $^{\circ}\mathrm{C}$ |
| Storage Temperature | Tstg | -55 to + | 150 | $^{\circ}\mathrm{C}$ |

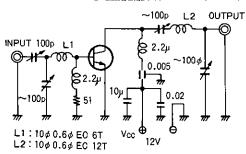
| Electrical Characteristics at Collector Cutoff Current | | V 40V I 0 | min | typ | max | unit |
|---|----------------------------------|---|-----|-------------|------|------|
| | Ісво | $V_{CB} = 40V, I_E = 0$ | | | 1.0 | μA |
| Emitter Cutoff Current | I_{EBO} | $V_{EB} = 4V, I_C = 0$ | | | 1.0 | μΑ |
| DC Current Gain | $\mathbf{h_{FE}} \divideontimes$ | $V_{CE} = 5V, I_C = 500mA$ | 60* | ĺ | 320% | K |
| Gain-Bandwidth Product | $\mathbf{f_T}$ | $V_{CE} = 10V, I_C = 50mA$ | 180 | 25 0 | | MHz |
| Output Capacitance | c _{ob} | $V_{CB} = 10V, f = 1MHz$ | | 15 | | рF |
| Output Power | Po | $V_{CC} = 12V, f = 27MHz$ | 1.0 | 1.8 | | w |
| | | Pin = 35mW | | | | |
| Collector Efficiency | η_c | See specified Test Circuit. | 60 | | | % |
| C-E Saturation Voltage | $V_{CE(sat)}$ | $I_C = 500 \text{mA}, I_B = 50 \text{mA}$ | | 0.2 | 0.6 | V |
| B-E Saturation Voltage | $V_{BE(set)}$ | $I_C = 500 \text{mA}, I_B = 50 \text{mA}$ | | 0.9 | 1.2 | V |
| C-B Breakdown Voltage | $V_{(BR)CBO}$ | $I_{\rm C} = 10 \mu A, I_{\rm E} = 0$ | 75 | | | V |
| C-E Breakdown Voltage | V _{(BR)CER} | $I_C = 1 \text{mA}, R_{BE} = 150 \Omega$ | 75 | | | V |
| C-E Breakdown Voltage | V _{(BR)CEO} | $I_C = 1 \text{mA}, R_{BE} = \infty$ | 45 | | | V |
| E-B Breakdown Voltage | V _{(BR)EBO} | $I_{\rm E} = 10 \mu A, I_{\rm C} = 0$ | 5 | | | V |

 $\ensuremath{\texttt{\%}}$: The 2SC4272 is classified by 500mA h_{FE} as follows :

| | | | | | | |
|----------|-----|---|-----|-------------|---|-----|
| 60 D 120 | 100 | E | 200 | 160 | F | 320 |

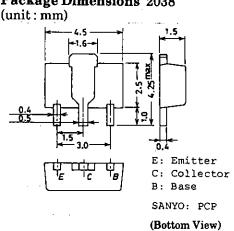
Marking: CH hFE rank: D,E,F

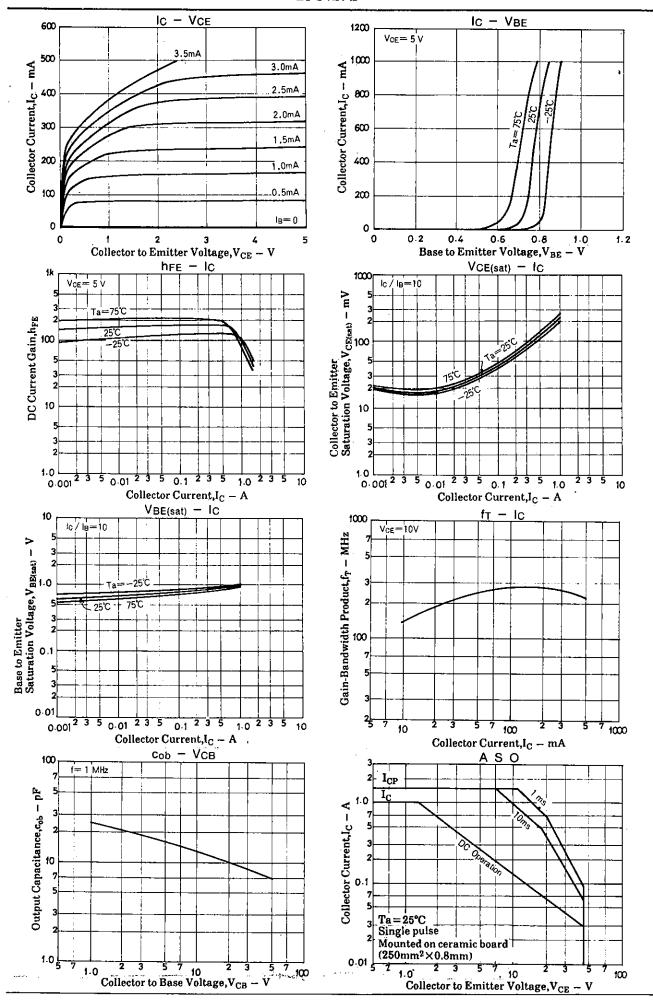
Collector Efficiency Test Circuit

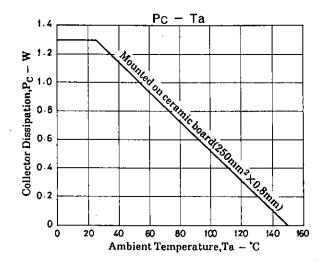


Unit (Resistance : Ω , Capacitance : F)

Package Dimensions 2038







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